Electronic Supplementary Information for

Reduced Graphene Oxide Decorated with Octahedral NiS_2/NiS Nanocrystals: Facile Synthesis and Tunable High Frequency Attenuation

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Table S1. The atomic percentage of Ni, S and C measured by XPS

Name	Atomic %
Ni 2p	7.66
S 2p	11.67
C 1s	80.67

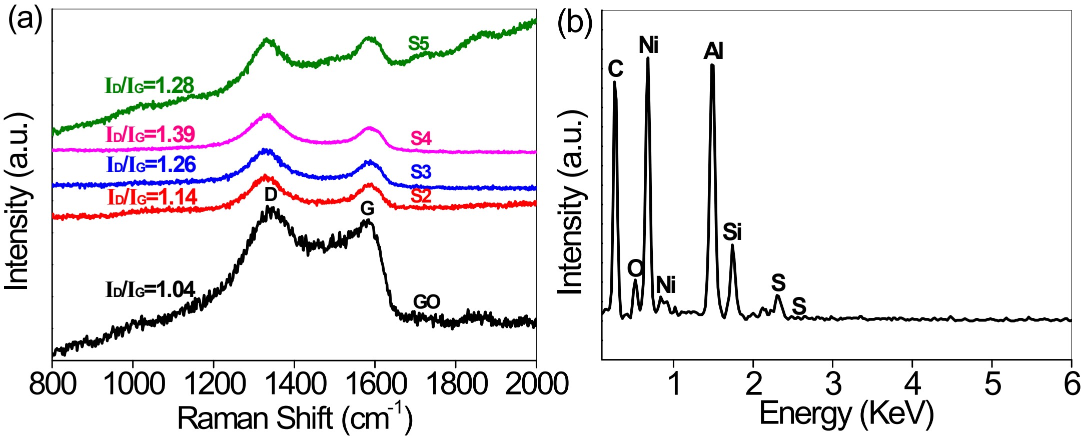

Fig. S1 (a) Raman spectrum of GO and S2-S4; (b) The EDS spectrum of NiS_2/NiS nanocrystals.

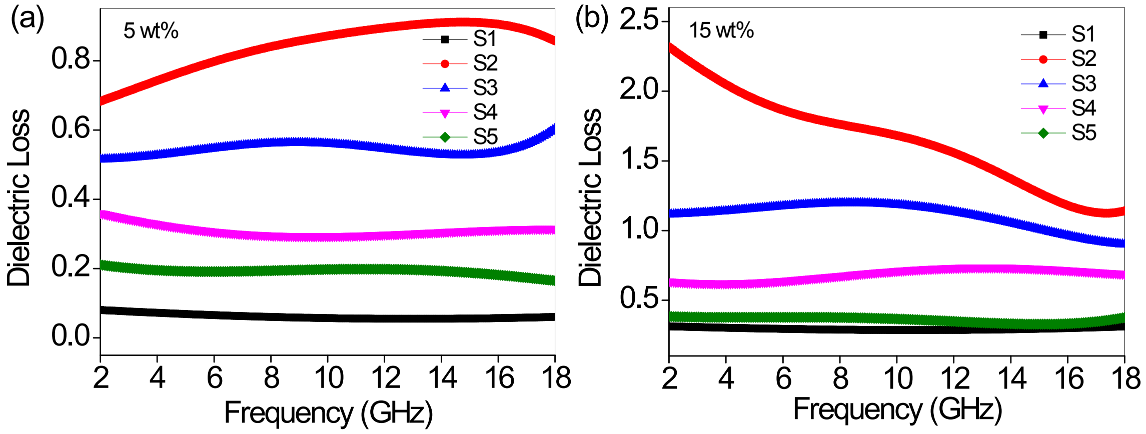

Fig. S2 Frequency dependence on dielectric loss for S1-S5 with loading content of (a) 5 wt% and (b) 15 wt%.

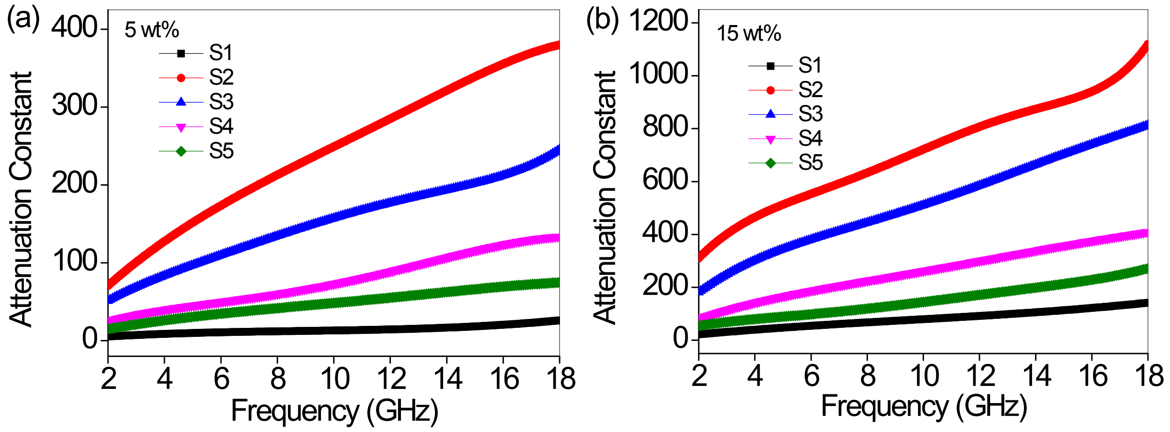

Fig.S3 Attenuation constant of the S1-S5 with loading content of (a) 5 wt% and (b) 15 wt%.